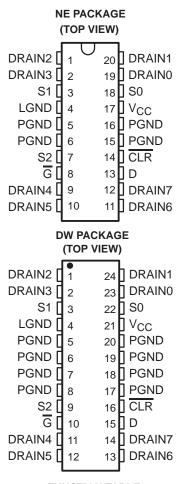
- Low r<sub>DS(on)</sub> . . . 1 Ω Typ
- Output Short-Circuit Protection
- Avalanche Energy . . . 75 mJ
- Eight 350-mA DMOS Outputs
- 50-V Switching Capability
- Four Distinct Function Modes
- Low Power Consumption

#### description

This power logic 8-bit addressable latch controls open-drain DMOS-transistor outputs and is designed for general-purpose storage applications in digital systems. Specific uses include working registers, serial-holding registers, and decoders or demultiplexers. This is a multifunctional device capable of operating as eight addressable latches or an 8-line demultiplexer with active-low DMOS outputs. Each open-drain DMOS transistor features an independent chopping current-limiting circuit to prevent damage in the case of a short circuit.

Four distinct modes of operation are selectable by controlling the clear ( $\overline{CLR}$ ) and enable ( $\overline{G}$ ) inputs as enumerated in the function table. In the addressable-latch mode, data at the data-in (D) terminal is written into the addressed latch. The addressed DMOS-transistor output inverts the data input with all unaddressed DMOS-transistor outputs remaining in their previous states. In the memory mode, all DMOS-transistor outputs remain in their previous states and are unaffected by the data or address inputs. To eliminate the possibility of entering erroneous data in the latch, enable G should be held high (inactive) while the address lines are changing. In the 8-line demultiplexing mode, the addressed output is inverted with respect to the D input and all other outputs are high. In the clear mode, all outputs are high and unaffected by the address and data inputs.

Separate power ground (PGND) and logic ground (LGND) terminals are provided to facilitate maximum system flexibility. All PGND terminals are internally connected, and each PGND terminal must be externally connected to the power system ground in order to minimize parasitic impedance. A single-point connection between LGND and PGND must be made externally in a manner that reduces crosstalk between the logic and load circuits.



#### **FUNCTION TABLE**

INPUTS		S	OUTPUT OF ADDRESSED	EACH OTHER	FUNCTION
CLR	G	D	DRAIN	DRAIN	TONOTION
Н	L	Н	L	Q <sub>io</sub>	Addressable
Н	L	L	Н	Q <sub>io</sub> Q <sub>io</sub>	Latch
Н	Н	Χ	Q <sub>io</sub>	Q <sub>io</sub>	Memory
L	L	Н	L	Н	8-Line
L	L	L	Н	Н	Demultiplexer
L	Н	Χ	Н	Н	Clear

#### **LATCH SELECTION TABLE**

SELE	CT IN	DRAIN	
S2	S1	S0	ADDRESSED
L	L	L	0
L	L	Н	1
L	Н	L	2
L	Н	Н	3
Н	L	L	4
Н	L	Н	5
Н	Н	L	6
Н	Н	Н	7

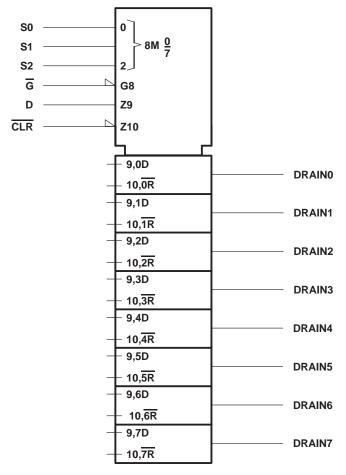
TEXAS INSTRUMENTS

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#### description (continued)

The TPIC6A259 is offered in a thermally-enhanced dual-in-line (NE) package and a wide-body, surface-mount (DW) package. The TPIC6A259 is characterized for operation over the operating case temperature range of  $-40^{\circ}$ C to  $125^{\circ}$ C.

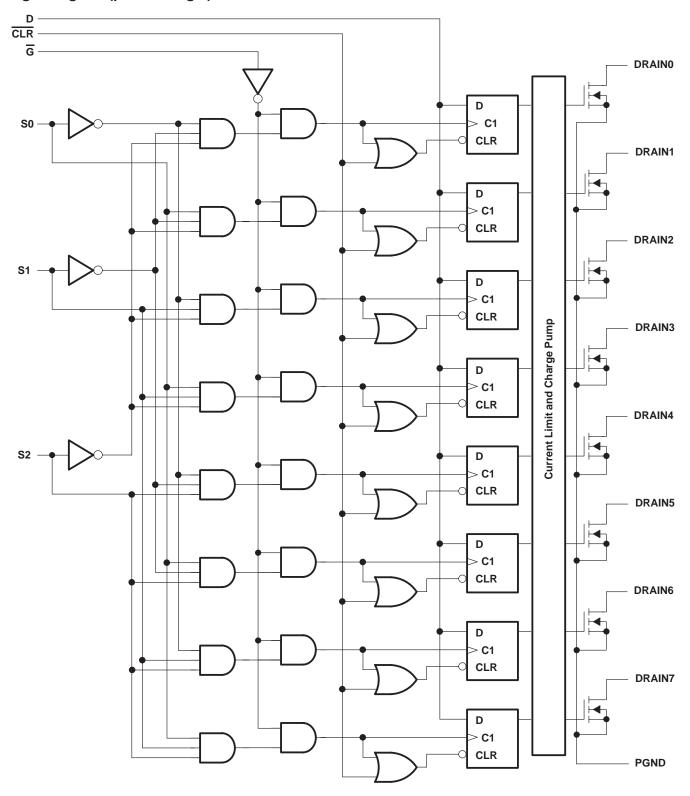
#### logic symbol<sup>†</sup>



<sup>&</sup>lt;sup>†</sup> This symbol is in accordance with ANSI/IEEE Std 91-1984 and IEC Publication 617-12.



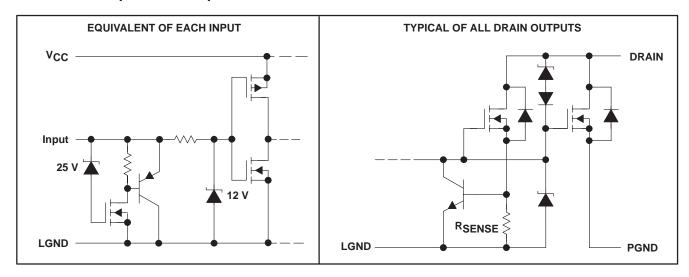
## logic diagram (positive logic)





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#### schematic of inputs and outputs



#### absolute maximum ratings over the recommended operating case temperature range (unless otherwise noted)†

Logic supply voltage, V <sub>CC</sub> (see Note 1)	7 V
Logic input voltage range, V <sub>I</sub>	0.3 V to 7 V
Power DMOS drain-to-source voltage, V <sub>DS</sub> (see Note 2)	50 V
Continuous source-to-drain diode anode current	1 A
Pulsed source-to-drain diode anode current (see Note 3)	2 A
Pulsed drain current, each output, all outputs on, $I_D$ , $T_C = 25^{\circ}C$ (see Note 3)	1.1 A
Continuous drain current, each output, all outputs on, ID. TC = 25°C	350 mA
Peak drain current single output, T <sub>C</sub> = 25°C (see Note 3)	1.1 A
Single-pulse avalanche energy, EAS (see Figure 6)	75 mJ
Avalanche current, I <sub>AS</sub> (see Note 4)	
Continuous total dissipation Se	ee Dissipation Rating Table
Operating virtual junction temperature range, T <sub>J</sub>	40°C to 150°C
Operating case temperature range, T <sub>C</sub>	40°C to 125°C
Storage temperature range, T <sub>stq</sub>	−65°C to 150°C
Lead temperature 1,6 mm (1/16 inch) from case for 10 seconds	

<sup>†</sup> Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

- NOTES: 1. All voltage values are with respect to LGND and PGND.
  - 2. Each power DMOS source is internally connected to PGND.
  - 3. Pulse duration  $\leq$  100  $\mu$ s, and duty cycle  $\leq$  2%.
  - 4. DRAIN supply voltage = 15 V, starting junction temperature ( $T_{JS}$ ) = 25°C, L = 210 mH, and  $I_{AS}$  = 600 mA (see Figure 6).

#### **DISSIPATION RATING TABLE**

PACKAGE	$T_C \le 25^{\circ}C$ POWER RATING	DERATING FACTOR ABOVE T <sub>C</sub> = 25°C	T <sub>C</sub> = 125°C POWER RATING
DW	1750 mW	14 mW/°C	350 mW
NE	2500 mW	20 mW/°C	500 mW



#### recommended operating conditions

	MIN	MAX	UNIT
Logic supply voltage, V <sub>CC</sub>	4.5	5.5	V
High-level input voltage, VIH	0.85 V <sub>CC</sub>	VCC	V
Low-level input voltage, V <sub>IL</sub>	0	0.15 V <sub>CC</sub>	V
Pulsed drain output current, T <sub>C</sub> = 25°C, V <sub>CC</sub> = 5 V (see Notes 3 and 5)	-1.8	0.6	Α
Setup time, D high before G↑,t <sub>SU</sub> (see Figure 2)	10		ns
Hold time, D high before G↑, th (see Figure 2)	5		ns
Pulse duration, t <sub>W</sub> (see Figure 2)	15		ns
Operating case temperature, T <sub>C</sub>	-40	125	°C

## electrical characteristics, $V_{CC}$ = 5 V, $T_{C}$ = 25°C (unless otherwise noted)

	PARAMETER	-	TEST CONDITIONS				MAX	UNIT
V(BR)DSX	Drain-to-source breakdown voltage	I <sub>D</sub> = 1 mA			50			V
V <sub>SD</sub>	Source-to-drain diode forward voltage	I <sub>F</sub> = 350 mA, See Note 3			0.8	1.1	V	
lн	High-level input current	$V_I = V_{CC}$					1	μΑ
I <sub>IL</sub>	Low-level input current	V <sub>I</sub> = 0	V <sub>I</sub> = 0				-1	μΑ
Icc	Logic supply current	I <sub>O</sub> = 0,	$I_O = 0$ , $V_I = V_{CC}$ or 0			0.5	5	mA
lok	Output current at which chopping starts	T <sub>C</sub> = 25°C,	; = 25°C, See Note 5 and Figures 3 and 4		0.6	0.8	1.1	Α
I <sub>(nom)</sub>	Nominal current	V <sub>DS(on)</sub> = 0.5 V, I <sub>(nom)</sub> = I <sub>D</sub> , T <sub>C</sub> = 85°C, V <sub>CC</sub> = 5 V, See Notes 5, 6, and 7			350		mA	
l <sub>a</sub>	Off-state drain current	$V_{DS} = 40 \text{ V},$	T <sub>C</sub> = 25°C			0.1	1	
ID	On-State drain current	$V_{DS} = 40 \text{ V},$	T <sub>C</sub> = 125°C			0.2	5	μΑ
r= 0 ( )	Static drain-to-source on-state	I <sub>D</sub> = 350 mA,	T <sub>C</sub> = 25°C	See Notes 5 and 6		1	1.5	Ω
rDS(on)	resistance	I <sub>D</sub> = 350 mA,	T <sub>C</sub> = 125°C	and Figures 9 and 10		1.7	2.5	52

## switching characteristics, $V_{CC} = 5 \text{ V}$ , $T_{C} = 25^{\circ}\text{C}$

	PARAMETER	TEST CONDITIONS	MIN	TYP	MAX	UNIT
tPHL	Propagation delay time, high- to low-level output from D			30		ns
tPLH	Propagation delay time, low- to high-level output from D	$C_L = 30 \text{ pF}, \qquad I_D = 350 \text{ mA},$		125		ns
t <sub>r</sub>	Rise time, drain output	See Figures 1, 2, and 11		60		ns
t <sub>f</sub>	Fall time, drain output			30		ns
ta	Reverse-recovery-current rise time	$I_F = 350 \text{ mA},   di/dt = 20 \text{ A/}\mu\text{s},$		100		ns
t <sub>rr</sub>	Reverse-recovery time	See Notes 5 and 6 and Figure 5		300		ns

NOTES: 3. Pulse duration  $\leq 100 \,\mu s$  and duty cycle  $\leq 2\%$ .

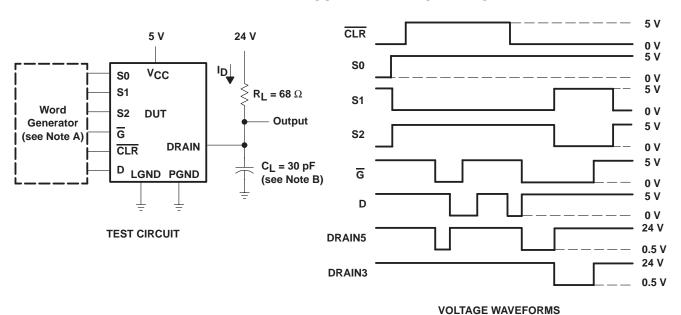
- 5. Technique should limit  $T_J T_C$  to 10°C maximum.
- 6. These parameters are measured with voltage-sensing contacts separate from the current-carrying contacts.
- Nominal current is defined for a consistent comparison between devices from different sources. It is the current that produces a voltage drop of 0.5 V at T<sub>C</sub> = 85°C.

#### thermal resistance

PARAMETER			TEST CONDITIONS	MIN	MAX	UNIT
Po 10	Thermal resistance, junction-to-case	DW	All eight outputs with equal power		10	°C/W
R <sub>0</sub> JC	Thermal resistance, junction-to-case	NE	All eight outputs with equal power		10	C/VV
Po	Thermal registeres junction to embient	DW	All eight outputs with equal newer		50	°C/W
$R_{\theta JA}$	Thermal resistance, junction-to-ambient		All eight outputs with equal power		50	~C/W



#### PARAMETER MEASUREMENT INFORMATION



**Figure 1. Typical Operation Mode** 

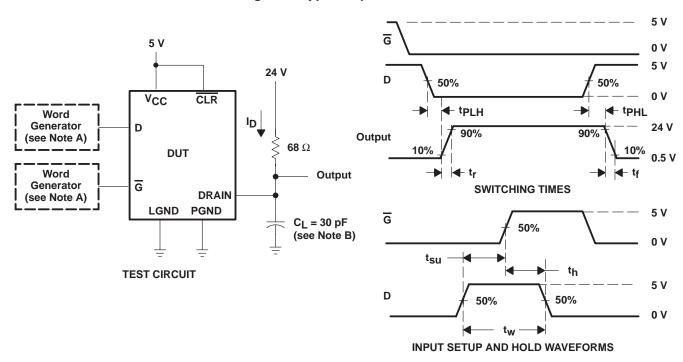


Figure 2. Test Circuit, Switching Times, and Voltage Waveforms

NOTES: A. The word generator has the following characteristics:  $t_{\Gamma} \le 10$  ns,  $t_{W} = 300$  ns, pulsed repetition rate (PRR) = 5 kHz,  $Z_{O} = 50 \ \Omega$ .

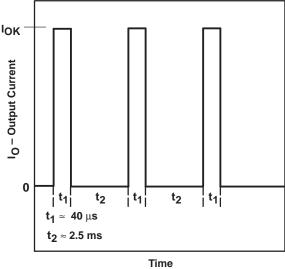
B. CL includes probe and jig capacitance.



#### PARAMETER MEASUREMENT INFORMATION

# TIME FOR INCREASING LOAD RESISTANCE 1.5 1.25 1.25 0.75 0.25 Region 1 Region 2

# REGION 1 CURRENT WAVEFORM



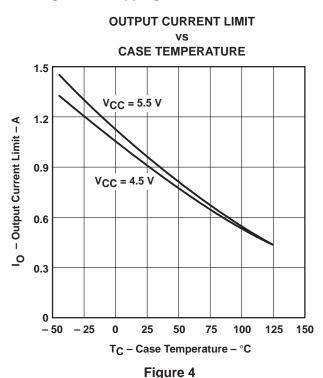
First output current pulses after turn-on in chopping mode with resistive load.

NOTES: A. Figure 3 illustrates the output current characteristics of the device energizing a load having initially low, increasing resistance, e.g., an incandescent lamp. In region 1, chopping occurs and the peak current is limited to I<sub>OK</sub>. In region 2, output current is continuous. The same characteristics occur in reverse order when the device energizes a load having an initially high, decreasing resistance.

B. Region 1 duty cycle is approximately 2%.

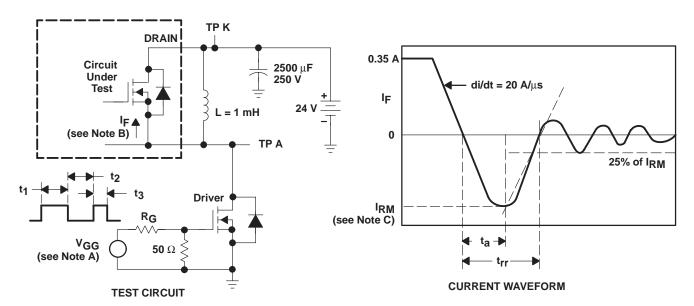
Time

Figure 3. Chopping-Mode Characteristics



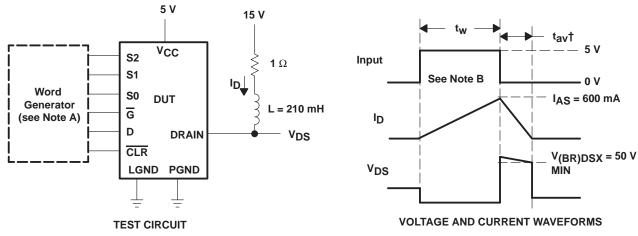


#### PARAMETER MEASUREMENT INFORMATION



- NOTES: A. The  $V_{GG}$  amplitude and  $R_{G}$  are adjusted for di/dt = 20 A/ $\mu$ s. A  $V_{GG}$  double-pulse train is used to set  $I_{F}$  = 0.35 A, where  $t_{1}$  = 10  $\mu$ s,  $t_2 = 7 \mu s$ , and  $t_3 = 3 \mu s$ .
  - B. The DRAIN terminal under test is connected to the TP K test point. All other terminals are connected together and connected to the TP A test point.
  - C. IRM = maximum recovery current

Figure 5. Reverse-Recovery-Current Test Circuit and Waveforms of Source-Drain Diode



† Non-JEDEC symbol for avalanche time.

- NOTES: A. The word generator has the following characteristics:  $t_r \le 10$  ns,  $t_f \le 10$  ns,
  - B. Input pulse duration,  $t_W$ , is increased until peak current  $I_{AS} = 600 \text{ mA}$ . Energy test level is defined as  $E_{AS} = (I_{AS} \times V_{(BR)DSX} \times t_{av})/2 = 75 \text{ mJ}.$

Figure 6. Single-Pulse Avalanche Energy Test Circuit and Waveforms



#### TYPICAL CHARACTERISTICS

# MAXIMUM CONTINUOUS DRAIN CURRENT OF EACH OUTPUT

# NUMBER OF OUTPUTS CONDUCTING SIMULTANEOUSLY

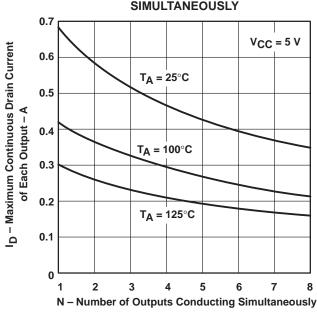


Figure 7

#### MAXIMUM PEAK DRAIN CURRENT OF EACH OUTPUT vs

# NUMBER OF OUTPUTS CONDUCTING SIMULTANEOUSLY

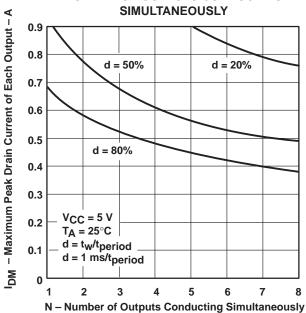


Figure 8

#### STATIC DRAIN-SOURCE ON-STATE RESISTANCE

vs **DRAIN CURRENT** 'DS(on) – Static Drain-Source On-State Resistance –  $\Omega$ 2  $V_{CC} = 5 V$ 1.75 See Note A T<sub>C</sub> = 125°C 1.5 **Current Limit** 1.25 T<sub>C</sub> = 25°C 1 0.75  $T_C = -40^{\circ}C$ 0.5 0.25 0 0 0.2 0.6 8.0 1 1.2

ID - Drain Current - A

Figure 9 NOTE A: Technique should limit  $T_J - T_C$  to 10°C maximum.

#### STATIC DRAIN-SOURCE ON-STATE RESISTANCE

# VS

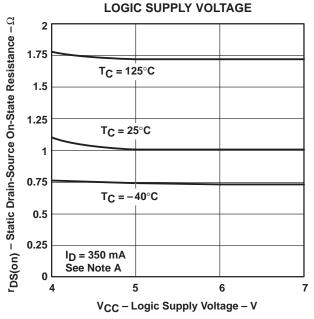


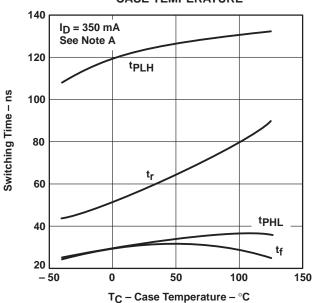
Figure 10



#### TYPICAL CHARACTERISTICS

# **SWITCHING TIME**



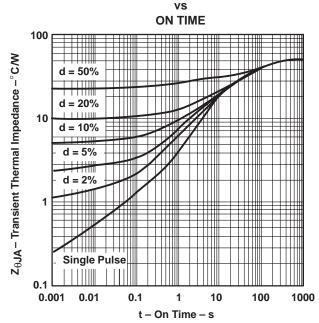


NOTE A: Technique should limit  $T_J - T_C$  to 10°C maximum.

Figure 11

#### THERMAL INFORMATION

### **NE PACKAGE** TRANSIENT THERMAL IMPEDANCE



The single-pulse curve represents measured data. The curves for various pulse durations are based on the following equation:

$$\begin{split} Z_{\theta JA} &= \left| \begin{array}{c} \frac{t_w}{t_c} \right| R_{\theta JA} + \left| \begin{array}{c} 1 - \frac{t_w}{t_c} \right| Z_{\theta}(t_w + t_c) \\ \\ &+ Z_{\theta}(t_w) - Z_{\theta}(t_c) \end{split}$$

Where:

$$\mathbf{Z}_{\theta}(\mathbf{t_{W}}) \ = \ \text{the single-pulse thermal impedance} \\ \text{for } \mathbf{t} = \ \mathbf{t_{W}} \ \text{seconds}$$

$$\mathbf{Z}_{\theta}\!\!\left(t_{\mathbf{C}}\right) \; = \; \text{the single-pulse thermal impedance} \\ \quad \text{for } t = \; t_{\mathbf{C}} \; \text{seconds}$$

$$\mathbf{Z}_{\theta}\!\!\left(t_{\mathbf{W}} + t_{\mathbf{C}}\right) = \text{ the single-pulse thermal impedance} \\ \text{ for } t = t_{\mathbf{W}} + t_{\mathbf{C}} \text{ seconds}$$

$$d = t_W/t_C$$

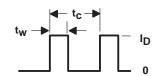


Figure 12







ti.com 29-May-2007

#### **PACKAGING INFORMATION**

Orderable Device	Status <sup>(1)</sup>	Package Type	Package Drawing	Pins	Package Qty	Eco Plan <sup>(2)</sup>	Lead/Ball Finish	MSL Peak Temp <sup>(3)</sup>
TPIC6A259DW	ACTIVE	SOIC	DW	24	25	TBD	CU NIPDAU	Level-1-220C-UNLIM
TPIC6A259DWG4	ACTIVE	SOIC	DW	24	25	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
TPIC6A259DWR	ACTIVE	SOIC	DW	24	2000	TBD	CU NIPDAU	Level-1-220C-UNLIM
TPIC6A259DWRG4	ACTIVE	SOIC	DW	24	2000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
TPIC6A259NE	ACTIVE	PDIP	NE	20	20	Pb-Free (RoHS)	CU NIPDAU	N / A for Pkg Type

<sup>(1)</sup> The marketing status values are defined as follows:

ACTIVE: Product device recommended for new designs.

LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

**NRND:** Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.

PREVIEW: Device has been announced but is not in production. Samples may or may not be available.

**OBSOLETE:** TI has discontinued the production of the device.

(2) Eco Plan - The planned eco-friendly classification: Pb-Free (RoHS), Pb-Free (RoHS Exempt), or Green (RoHS & no Sb/Br) - please check http://www.ti.com/productcontent for the latest availability information and additional product content details.

TBD: The Pb-Free/Green conversion plan has not been defined.

**Pb-Free** (RoHS): TI's terms "Lead-Free" or "Pb-Free" mean semiconductor products that are compatible with the current RoHS requirements for all 6 substances, including the requirement that lead not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, TI Pb-Free products are suitable for use in specified lead-free processes.

**Pb-Free (RoHS Exempt):** This component has a RoHS exemption for either 1) lead-based flip-chip solder bumps used between the die and package, or 2) lead-based die adhesive used between the die and leadframe. The component is otherwise considered Pb-Free (RoHS compatible) as defined above.

**Green (RoHS & no Sb/Br):** TI defines "Green" to mean Pb-Free (RoHS compatible), and free of Bromine (Br) and Antimony (Sb) based flame retardants (Br or Sb do not exceed 0.1% by weight in homogeneous material)

(3) MSL, Peak Temp. -- The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.

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# DW (R-PDSO-G24)

## PLASTIC SMALL-OUTLINE PACKAGE



NOTES:

- A. All linear dimensions are in inches (millimeters).
- B. This drawing is subject to change without notice.
- C. Body dimensions do not include mold flash or protrusion not to exceed 0.006 (0,15).
- D. Falls within JEDEC MS-013 variation AD.



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